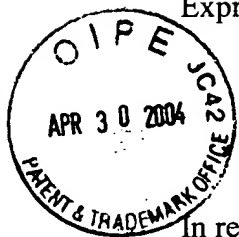


#13B

Express Mail Label No. EV 384 066 449 US

PATENT APPLICATION

Docket No. 15313.1



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hsiang-Lan Lung

RECEIVED

MAY 06 2004

Serial No.: 09/882,480

OFFICE OF PETITIONS

) Art Unit
) 2814

Filed: June 14, 2001

Confirmation No.: 8120

For: HIGH DENSITY SINGLE TRANSISTOR
FERROELECTRIC NON-VOLATILE MEMORY

Examiner: Marcos D. Pizarro-Crespo

PRELIMINARY AMENDMENT

Mail Stop: PETITIONS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This communication is in response to Examiner's Office Action mailed May 16, 2003 (the "Office Action"). Reconsideration is respectfully requested in view of the following amendments and remarks.

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims that begins on page 3 of this paper.

Remarks/Arguments begin on page 15 of this paper.